

N-channel 60 V, 8.7 mΩ logic level MOSFET in LFPAK56 8 May 2013

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications 3.

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching •

Quick reference data 4.

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	86	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	147	W
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 11</u>		-	6.8	8.7	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 48 \text{ V};$ T _j = 25 °C; Fig. 13; Fig. 14		-	9.7	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UTA
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9Y8R7-60E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y8R7-60E	98E760

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][<u>2]</u>	-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	86	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	61	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 4		-	346	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	147	W

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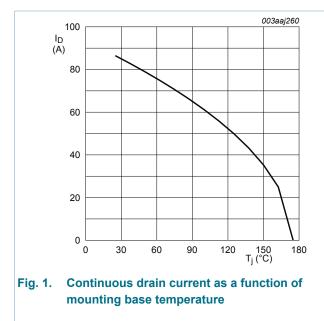
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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode	,				
I _S	source current	T _{mb} = 25 °C		-	86	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	346	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 86 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped; Fig. 3	[3][4]	-	76.5	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [1]
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]



 $V_{GS} \ge 5V$

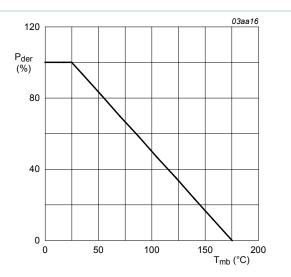
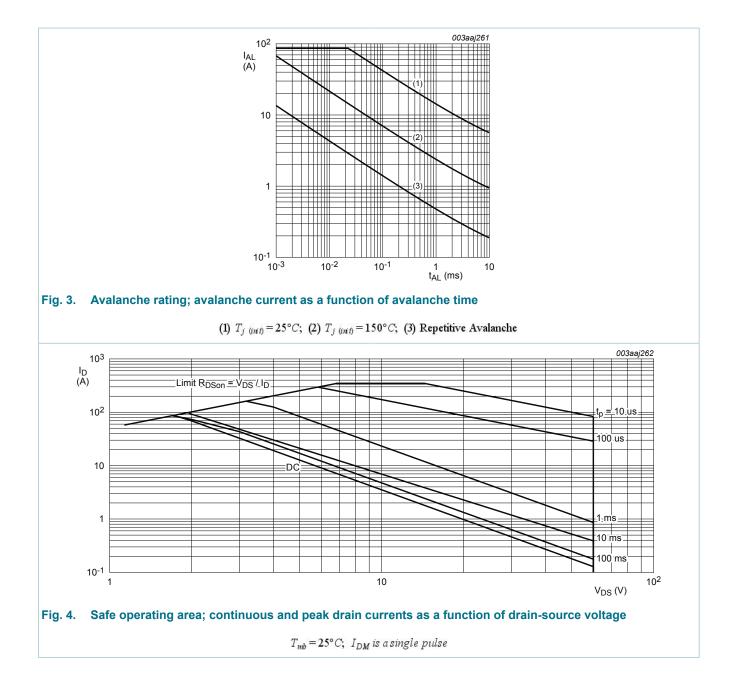


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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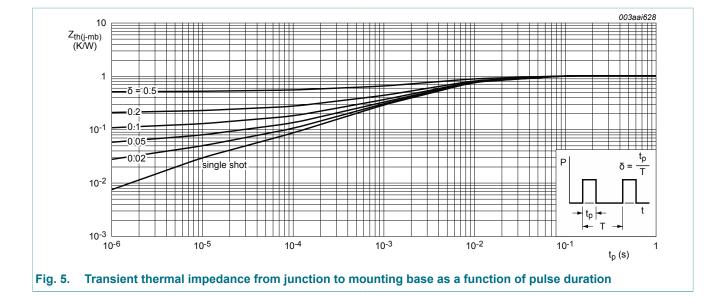
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9. Thermal characteristics

Table 6. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.02	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	$\frac{I_{D} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}}{I_{D} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_{j} = -55 \ ^{\circ}\text{C}} \qquad 60 \qquad -$ $\frac{I_{D} = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_{j} = -55 \ ^{\circ}\text{C}}{54} \qquad -$ $\frac{I_{D} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad 1.4 \qquad 1.7$ $\frac{I_{D} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_{j} = -55 \ ^{\circ}\text{C}; \qquad - \qquad -$ $\frac{I_{D} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_{j} = -55 \ ^{\circ}\text{C}; \qquad - \qquad -$ $\frac{I_{D} = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_{j} = 175 \ ^{\circ}\text{C}; \qquad 0.5 \qquad - \qquad -$ $\frac{I_{D} = 1 \ \text{mA}; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 0.05$ $\frac{V_{DS} = 60 \ V; \ V_{GS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 0.05$ $\frac{V_{DS} = 60 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 2$ $\frac{V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 2$ $\frac{V_{GS} = 5 \ V; \ I_{D} = 20 \ A; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 68$ $\frac{V_{GS} = 5 \ V; \ I_{D} = 20 \ A; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 68$ $\frac{V_{GS} = 5 \ V; \ I_{D} = 20 \ A; \ T_{j} = 25 \ ^{\circ}\text{C}; \qquad - \qquad 68$ $\frac{V_{GS} = 5 \ V; \ I_{D} = 20 \ A; \ T_{j} = 175 \ ^{\circ}\text{C}; \qquad - \qquad 68$	-	-	V	
V _{GS(th)} gate-source voltage	gate-source threshold voltage		1.4	1.7	2.1	V
	,		-	-	2.45	V
		,	0.5	-	-	V
I _{DSS} drain leakage current	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
	gate leakage current	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 11</u>	-	6.8	8.7	mΩ
	resistance	· - · , · ·	-	6	7.5	mΩ
			-	-	19.7	mΩ
Dynamic cl	naracteristics	· · ·	I			
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	31	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	9	-	nC

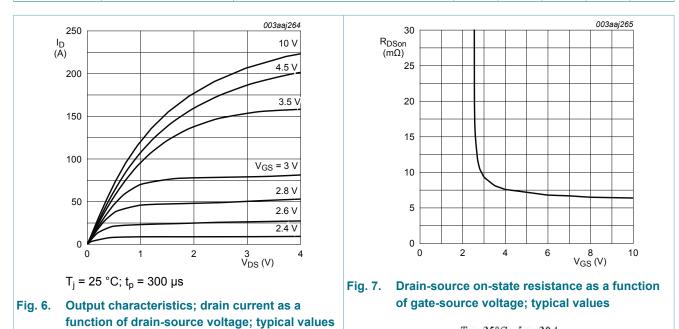
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Qr

recovered charge

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge		-	9.7	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	3435	4570	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	295	355	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 45 V; R _L = 2 Ω; V _{GS} = 5 V;	-	150	205	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 2 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	17	-	ns
t _r	rise time		-	30	-	ns
t _{d(off)}	turn-off delay time		-	42	-	ns
t _f	fall time		-	26	-	ns
Source-dra	in diode	· · · · ·	I			
V _{SD}	source-drain voltage	I_{S} = 20 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	24	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	_	22.3	_	nC

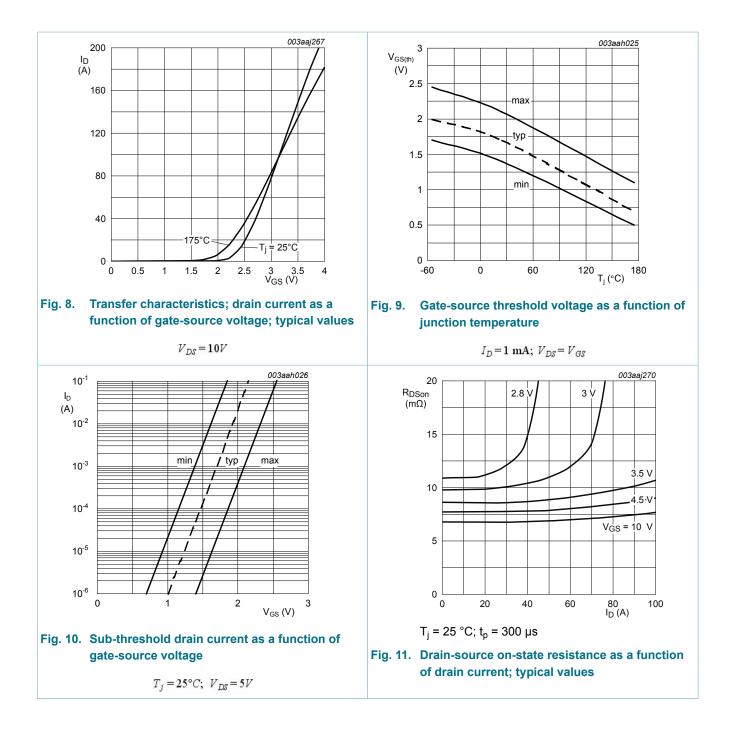


 $T_i = 25^{\circ}C; I_D = 20A$

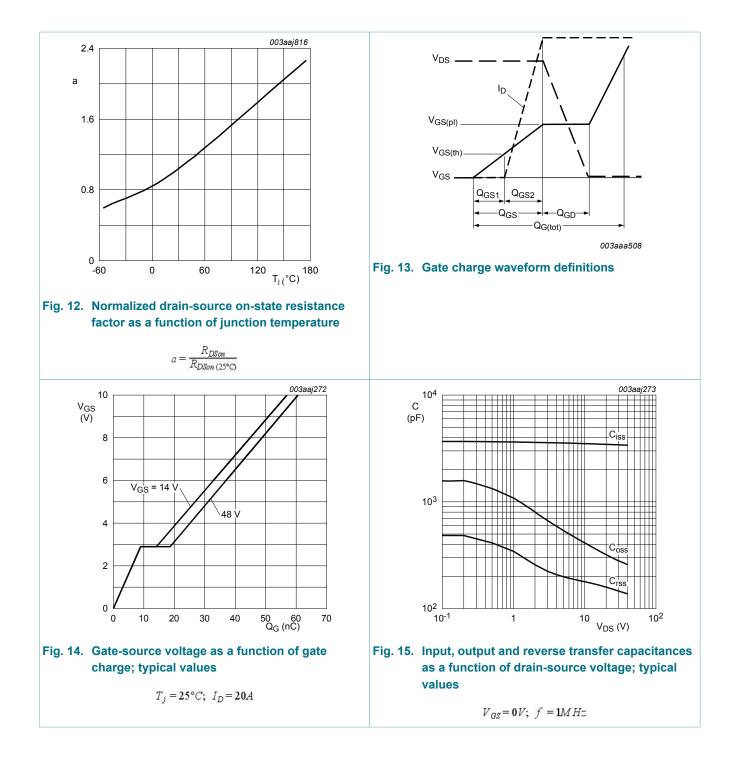
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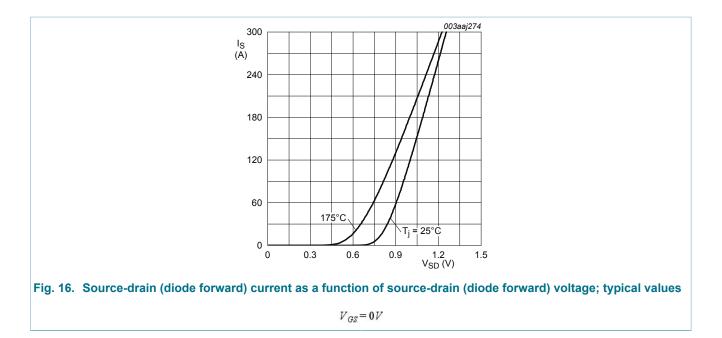


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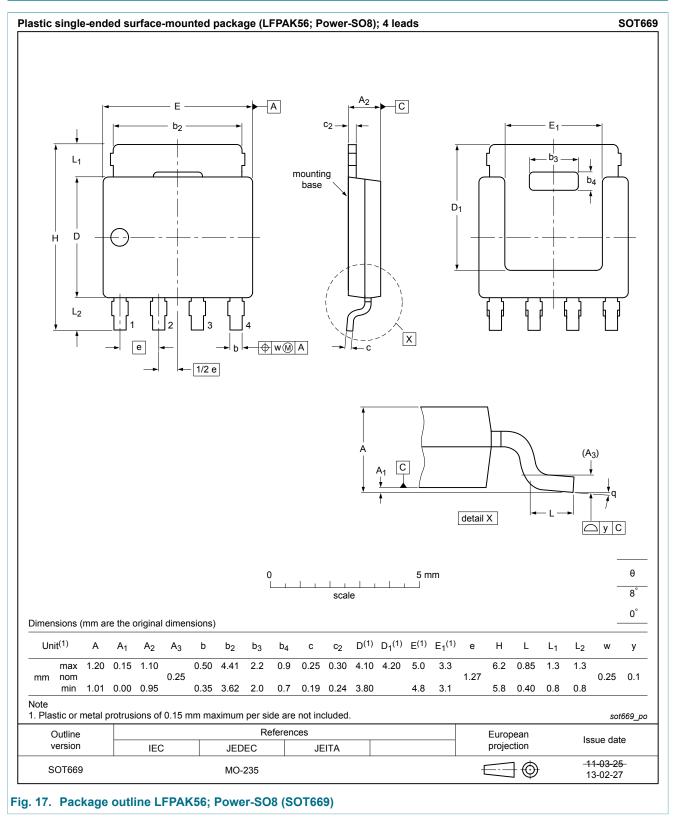
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11. Package outline



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